

IFW

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q77954

Fumio MATSUMOTO

Appln. No.: 10/575,081

Group Art Unit: Not Yet Assigned

Confirmation No.: Not Yet Assigned

Examiner: Not Yet Assigned

Filed: April 7, 2006

For:

COMPOUND SEMICONDUCTOR SINGLE CRYSTAL AND PRODUCTION

PROCESS THEREOF

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §§ 1.97 and 1.98

MAIL STOP AMENDMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and/or listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

One copy of each of the listed documents is submitted herewith, except for the following: U.S. patents and/or U.S. patent publications; and co-pending non-provisional U.S. applications filed after June 30, 2003.

The present Information Disclosure Statement is being filed: (1) No later than three months from the application's filing date; (2) Before the mailing date of the first Office Action on the merits (whichever is later); or (3) Before the mailing date of the first Office Action after

Q77954

...INFORMATION DISCLOSURE STATEMENT

U.S. Appln. No.: 10/575,081

filing a request for continued examination (RCE) under §1.114, and therefore, no Statement

under 37 C.F.R. § 1.97(e) or fee under 37 C.F.R. § 1.17(p) is required.

In compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for

foreign language documents, Applicant submits an English language Abstract and machine

translation for JP 10-87392, and partial English translations for "Technique for Growing Bulk

Crystal" and "Crystal Growth of Compound Semiconductors and Its Evaluation No. 6".

The submission of the listed documents is not intended as an admission that any such

document constitutes prior art against the claims of the present application. Applicant does not

waive any right to take any action that would be appropriate to antedate or otherwise remove any

listed document as a competent reference against the claims of the present application.

The USPTO is directed and authorized to charge all required fees, except for the Issue

Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any

overpayments to said Deposit Account.

Respectfully submitted,

Registration No. 33,276

Abraham J. Rosner

SUGHRUE MION, PLLC

Telephone: (202) 293-7060

Facsimile: (202) 293-7860

WASHINGTON OFFICE

23373

CUSTOMER NUMBER

Date: June 19, 2006

2

Substitute for Form 1440 A & DIDTO		Complete if Known		
Substitute for Form 1449 A & B/PTO		Application Number	10/575,081	
STATEMENT BY APPLICANT		Confirmation Number	Not Yet Assigned	
STATEMENT BY APPLICANT		Filing Date	April 7, 2006	
DUN 1 9 2006 STATEMENT BY APPLICANT		First Named Inventor	Fumio MATSUMOTO	
(use as many sheets as necessary)	Art Unit	Not Yet Assigned		
	Examiner Name	Not Yet Assigned		
TRADE Reet 1 of 1	·	Attorney Docket Number	Q77954	

U.S. PATENT DOCUMENTS						
Examiner Cite Initials* No.1	Cito	Document	Number	Publication Date MM-DD-YYYY		
		Number	Kind Code ² (if known)		Name of Patentee or Applicant of Cited Document	
		US				
		US				
		US				
		US				
		US				
		US				
		US				
		US				
		US				

FOREIGN PATENT DOCUMENTS							
Examiner Cite Initials* No.1	Foreign Patent Document			Publication Date	Name of Patentee or		
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)	MM-DD-YYYY	Applicant of Cited Document	Translation ⁶
		JP	10-87392		04-07-1998	JAPAN ENERGY CORP	Abstract
		-					_
				 	-		<u> </u>
		+					
							
							_
·		1		1			

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶	
		Keigo HOSHIKAWA; "Technique for Growing Bulk Crystal"; Advanced Electronics Series I-4; Baifukan Publishing Co.; 1994; pp. 238-241	Yes	
		Jun-ichi NISHIZAWA; "Crystal Growth of Compound Semiconductors and its Evaluation No. 6"; Journal of Semiconductor Research; Vol. 35; August 5, 1991; pp. 16-19	Yes	

Examiner Signature	 	Date Considered	

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or follow the hyperlink from the title of the document to the intranet. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to indicate here if English language Translation is attached.